Abstracts

A monolithic Si PCS-CDMA power amplifier with an impedance-controllable biasing scheme

Sifen Luo and T. Sowlati. "A monolithic Si PCS-CDMA power amplifier with an impedance-controllable biasing scheme." 2001 Radio Frequency Integrated Circuits (RFIC) Symposium 01. (2001 [RFIC]): 217-220.

This paper for the first time presents a monolithic Si PCS-CDMA power amplifier (PA) capable of delivering 28.2 dBm output power with 30% power-added efficiency (PAE) and -45 dBc adjacent-channel-power ratio (ACPR) at 1.9 GHz and 3.6 V supply voltage. The PA implemented in a 30 GHz BiCMOS process incorporates a novel impedance-controllable biasing scheme to control class of operation and bias impedance of the output stage.

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